

SSS15N06/05

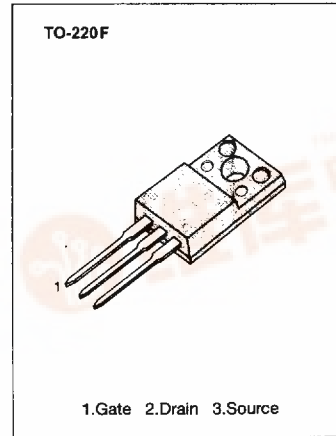
N-CHANNEL POWER MOSFETS

FEATURES

- Lower $R_{DS(on)}$
- Improved inductive ruggedness
- Fast switching times
- Rugged polysilicon gate cell structure
- Lower input capacitance
- Extended safe operating area
- Improved high temperature reliability

PRODUCT SUMMARY

Part Number	Vds	RDS(on)	Id
SSS15N06	60V	0.084 Ω	14A
SSS15N05	50V	0.084 Ω	14A



ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	SSS15N06	SSS15N05	Unit
Drain-Source Voltage (1)	V _{DSS}	60	50	V _{dc}
Drain-Gate Voltage (R _{GS} =1.0M Ω)(1)	V _{DGR}	60	50	V _{dc}
Gate-Source Voltage	V _{GS}	± 20		V _{dc}
Continuous Drain Current T _c =25 °C	I _D	14		A _{dc}
Continuous Drain Current T _c =100 °C	I _D	9.8		A _{dc}
Drain Current - Pulsed (3)	I _{DM}	64		A _{dc}
Gate Current - Pulsed	I _{GM}	± 1.5		A _{dc}
Single Pulsed Avalanche Energy (4)	E _{AS}	7.5		mJ
Avalanche Current	I _{AS}	14		A
Total Power Dissipation at T _c =25 °C	P _D	37		Watts
Derate above 25 °C		0.25		
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-55 to +175		°C
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 seconds	T _L	300		°C

Notes : (1) T_J=25°C to 175°C

(2) Pulse test : Pulse width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

(3) Repetitive rating : Pulse width limited by max. junction temperature

(4) L=100 μH , V_{dd}=25V, R_G=25 Ω , Starting T_J=25°C



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ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-Source Breakdown Voltage					
	SSS15N06	60	-	-	V	V _{GS} =0V, I _D =250μA
	SSS15N05	50	-	-	V	
V _{GS(th)}	Gate Threshold Voltage	2.0	-	4.0	V	V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	Gate-Source Leakage Forward	-	-	100	nA	V _{GS} =20V
I _{GSS}	Gate-Source Leakage Reverse	-	-	-100	nA	V _{GS} =-20V
I _{DSS}	Zero Gate Voltage Drain Current	-	-	250	μA	V _{DS} =Max. Rating, V _{GS} =0V
		-	-	1000	μA	V _{DS} =0.8 Max. Rating, V _{GS} =0V, T _C =150°C
R _{DS(on)}	Static Drain-Source On Resistance(2)	-	-	0.084	Ω	V _{GS} =10V, I _D =8A
g _{fS}	Forward Transconductance (2)	5.6	-	-	Ω	V _{DS} ≥50V, I _D =8A
C _{iss}	Input Capacitance	-	635	-	pF	V _{GS} =0V, V _{DS} =25V, f=1.0MHz
C _{oss}	Output Capacitance	-	218	-	pF	
C _{rss}	Reverse Transfer Capacitance	-	105	-	pF	
t _{d(on)}	Turn-On Delay Time	-	-	30	ns	V _{DD} =0.5BV _{DSS} , I _D =16A, Z _O =24Ω (MOSFET switching times are essentially independent of operating temperature)
t _r	Rise Time	-	-	90	ns	
t _{d(off)}	Turn-Off Delay Time	-	-	40	ns	
t _f	Fall Time	-	-	30	ns	
Q _g	Total Gate Charge (Gate-Source Plus Gate-Drain)	-	-	33	nC	
Q _{gs}	Gate-Source Charge	-	6.3	-	nC	V _{GS} =10V, I _D =16A, V _{DS} =0.8 Max. Rating (Gate charge is essentially independent of operating temperature)
Q _{gd}	Gate-Drain ("Miller") Charge	-	12.3	-	nC	

THERMAL RESISTANCE

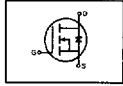
Symbol	Characteristics		All	Units	Remark
R _{thJC}	Junction-to-Case	MAX	4.0	K/W	
R _{thCS}	Case-to-Sink	TYP	0.5	K/W	Mounting surface flat smooth, and greased
R _{thJA}	Junction-to-Ambient	MAX	62.5	K/W	Free Air Operation

Notes : (1) T_J=25°C to 175°C

(2) Pulse test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%

(3) Repetitive rating : Pulse width limited by max. junction temperature

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	-	-	50	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier 
I _{SM}	Pulse Source Current (Body Diode) (3)	-	-	200	A	
V _{SD}	Diode Forward Voltage (2)	-	-	2.5	V	T _J =25°C, I _S =16A, V _{GS} =0V
t _r	Reverse Recovery Time	-	-	250	ns	T _J =25°C, I _F =16A, dI _F /dt=100A/μS

- Notes : (1) T_J=25°C to 175°C
 (2) Pulse test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%
 (3) Repetitive rating : Pulse width limited by max. junction temperature

